Features

- 500-mA-Rated Collector Current(single output)
- High-Voltage Outputs:50V
- Output Clamp Diodes

General Description

The HX2003 is high-voltage high-current Darlington transistor arrays each containing seven open collector common emitter pairs. Each pair is rated at 500mA. Suppression diodes are included for inductive load driving, the inputs and outputs are pinned in opposition to simplify board layout.

• Inputs Compatible With Various Types of Logic

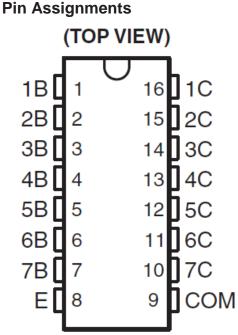
Relay-Driver Applications

These devices are capable of driving a wide range of loads including solenoids, relays, DC motors, LED displays, filament lamps, thermal print-heads and high-power buffers.

The HX2003 is available in both a small outline 16-pin package (DIP16, SOP16, SSOP16 and TSSOP16).

10 7C

Connection Diagram



сом 16 1C 1B 15 2F 2C 14 зC 3B 13 4C 4B 12 5B 5C 11 6C 6B

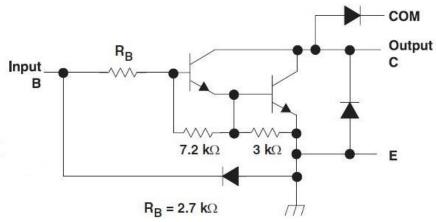
LOGIC DIAGRAM



Pin Descriptions

Pin Number	Pin Name	Function
1	1B	Input pair1
2	2B	Input pair1
3	3B	Input pair1
4	4B	Input pair1
5	5B	Input pair1
6	6B	Input pair1
7	7B	Input pair1
8	E	Common Emitter (ground)
9	СОМ	Common Clamp Diodes
10	7C	Output pair7
11	6C	Output pair6
12	5C	Output pair5
13	4C	Output pair4
14	3C	Output pair3
15	2C	Output pair2
16	1C	Output pair1

Functional Block Diagram



Note: All resistor values shown are nominal.

The collentor-emitter diode is a parasitic structure and should not be used to conduct current. If the collector(s) go below ground an external Schoottky diode should be added to clamp negative undershoots.

Absolute Maximum Ratings ⁽¹⁾

At 25°C free-air temperature (unless otherwise noted)

Symbol	Parameter		Min	Max	Unit
Vcc	Collector to emitter voltage			50	V
V _R	Clamp diode reverse voltage(2)			50	V
VI	Input voltage(2)			30	V
I _{CP}	Peak collector current	See typical characteristics		500	mA
Ι _{οκ}	Output clamp current			500	mA
I _{TE}	Total emitter-terminal current			-2.5	А
T _A	Operating free-air temperature range	TX2003	-40	+105	°C
θ_{JA}	Thermal Resistance Junction	n-to-Ambient(3)		63	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case(4)			12	0/11
TJ	Operating virtual junction temperature			+150	°C
T _{STG}	Storage temperature range			+150	°C
ESD	Human Body Mode			3000	V

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.
- (3) Maximum power dissipation is a function of TJ(max), θJA, and TA. The maximum allowable power dissipation at any allowable ambient temperature is PD = (TJ(max) – TA)/θJA. Operating at the absolute maximum TJ of 150°C can affect reliability.
- (4) Maximum power dissipation is a function of TJ(max), θJC, and TA. The maximum allowable power dissipation at any allowable ambient temperature is PD = (TJ(max) – TA)/θJC. Operating at the absolute maximum TJ of 150°C can affect reliability.

Recommended Operating Conditions

Symbol	Parameter		Max	Unit
VCC	Collector to Emitter voltage	-	50	V
TA	Operating Ambient Temperature	-40	+105	°C

Parameter		Test	Test Conditions		TX2003A			Unit
	Parameter	Figure		MIN	TYP	MAX	Unit	
	On-state input voltage	Figure 6		IC = 200 mA			2.4	
V _{I(on)}			Figure 6 VCE = 2 V	IC = 250 mA			2.7	V
				IC = 300 mA			3	
			II = 250 µA,	IC = 100 mA	-	0.9	1.1	
V _{CE(sat)}	Collector-emitter saturation voltage	Figure 5	II = 350 µA,	IC = 200 mA		1	1.3	V
	5		II = 500 μA,	IC = 350 mA		1.2	1.6	
	Collector cutoff current	Figure 1	VCE = 50 V,	II = 0			50	
I _{CEX}		Figure 2	VCE = 50 V, TA = +105°C	II = 0			100	μA
V _F	Clamp forward voltage	Figure 8	IF = 350 mA			1.7	2	V
l I(off)	Off-state input current	Figure 3	VCE = 50 V,	IC = 500 µA	50	65		μA
			VI = 3.85 V			0.93	1.35	
П	Input current	Figure 4	VI = 5 V					mA
			VI = 12 V					
15		Figure 7					50	
IR	Clamp reverse current	Figure 7	VR = 50 V	TA = 70°C			100	μA
Ci	Input capacitance		VI = 0, f = 1 MHz			15	25	pF

Electrical Characteristics(TA=+25°C, unless otherwise specified)

Switching Characteristics (TA = +25°C, unless otherwise specified)

Parameter		Test Conditions	TX2003			UNIT
			MIN	TYP	MAX	
t _{PLH}	Propagation delay time, low- to high-level output	See Figure 9		0.25	1	μs
t PHL	Propagation delay time, high- to low-level output	See Figure 9		0.25	1	μs
V _{OH}	High-level output voltage after switching	VS = 50 V, IO = 300 mA, See Figure 9	VS-20			mV

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Parameter Measurement Information

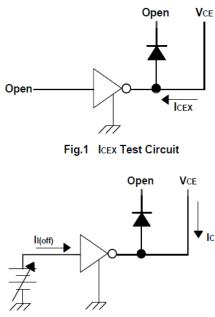


Fig.3 II(off) Test Circuit

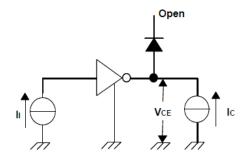
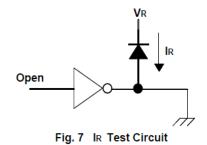


Fig. 5 hFE , VCE(sat) Test Circuit



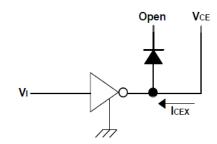


Fig.2 ICEX Test Circuit

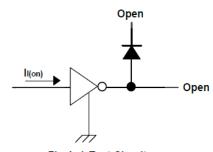


Fig.4 II Test Circuit

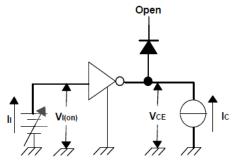


Fig. 6 VI(on) Test Circuit

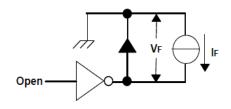
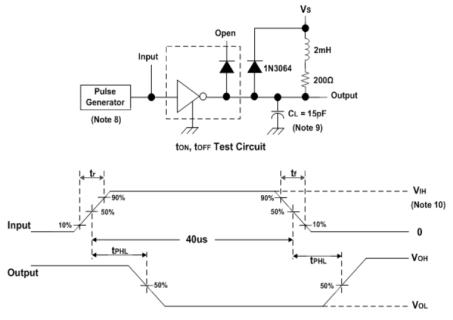


Fig. 8 VF Test Circuit



Voltage Waveform

Fig. 9 Latch-Up Test Circuit and Voltage Waveform

Notes: 8. The pulse generator has the following characteristics:

Pulse Width=12.5Hz, output impedance 50Ω, tr≤5ns, tr≤10ns.

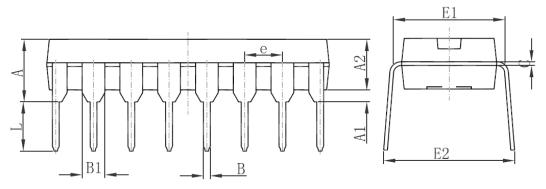
9. C_L includes prove and jig capacitance.

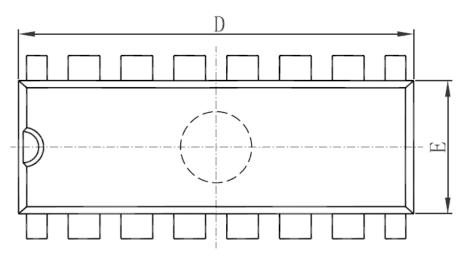
10. V_{IH}=3V

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HX2003 series High-voltage High-current Darlington Transistor Arrays

DIP16 Outline Dimensions

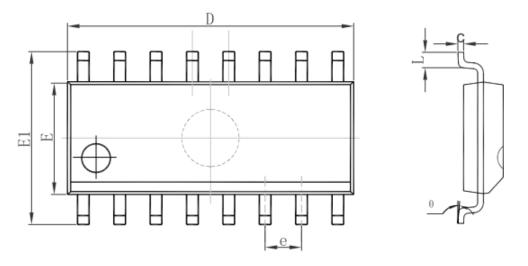


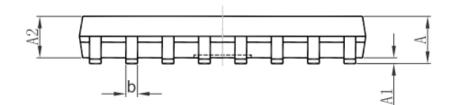


Cumb a l	Dimensions Ir	n Millimeters	Dimensions	In Inches		
Symbol	Min	Max	Min	Max		
А	3. 710	4.310	0.146	0. 170		
A1	0. 510		0. 020			
A2	3.200	3.600	0. 126	0. 142		
В	0. 380	0. 570	0.015	0. 022		
B1	1. 524	1. 524 (BSC)		0. 060 (BSC)		
С	0. 204	0.360	0.008	0. 014		
D	18.800	19.200	0. 740	0. 756		
E	6.200	6.600	0. 244	0. 260		
E1	7.320	7.920	0. 288	0. 312		
е	2. 540 (BSC)		0.100	(BSC)		
L	3.000	3.600	0.118	0. 142		
E2	8.400	9.000	0. 331	0. 354		



SOP16 Outline Dimensions

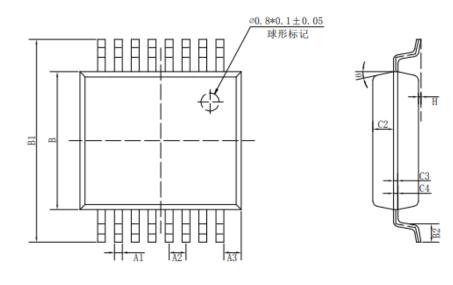


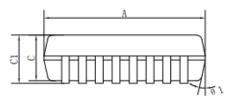


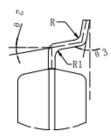
Courts of	Dimensions In Millimeters		Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	1. 350	1. 750	0. 053	0. 069
A1	0. 100	0. 250	0.004	0. 010
A2	1. 350	1. 550	0. 053	0. 061
b	0. 330	0. 510	0. 013	0. 020
С	0. 170	0. 250	0. 007	0. 010
D	9.800	10. 200	0. 386	0. 402
E	3. 800	4. 000	0. 150	0. 157
E1	5.800	6. 200	0. 228	0. 244
е	1. 270	(BSC)	0. 050	(BSC)
L	0. 400	1. 270	0. 016	0. 050
θ	0 °	8°	0°	8°



SSOP16 Outline Dimensions





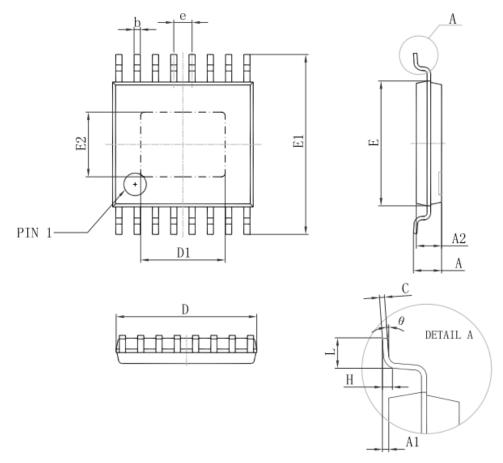


尺寸 标注	最小(mm)	最大(mm)	尺寸 标注	最小(mm)	最大(mm)
A	6.15	6.25	C3	0.	152
A1	0.3	0TYP	C4	0.	172
A2	0. 6	5TYP	Н	0.05	0.15
A3	0.6	75TYP	θ	12° TYP4	
В	5. 25	5.35	θ1	12	° TYP4
B1	7.65	7.95	θ 2	10	°TYP
B2	0.60	0.80	θ3	$0^{\circ} \sim 8^{\circ}$	
С	1.70	1.80	R	0. 20TYP	
C1	1.75	1.95	R1	0.15TYP	
C2	0. 7	99			

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HX2003 series High-voltage High-current Darlington Transistor Arrays

TSSOP16 Outline Dimensions



Symbol	Dimensions In	Millimeters	Dimension	s In Inches
Symbol	Min	Max	Min	Max
D	4.900	5.100	0.193	0.201
D1	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
с	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
E2	2.200	2.400	0.087	0.094
А		1.150		0.043
A2	0.800	1.000	0.031	0.039
A1	0.020	0.150	0.001	0.006
e	0.65 (BSC)		0.026	(BSC)
L	0.500	0.700	0.02	0.028
Н	0.25(TYP)		0.01(TYP)	
θ	1°	7 °	1 °	7 °